



STD10NM65N - STF10NM65N STP10NM65N - STU10NM65N

N-channel 650 V - 0.43 Ω - 9 A - TO-220 - TO-220FP- IPAK - DPAK
second generation MDmesh™ Power MOSFET

Features

| Type | V _{DSS} (@T _{jmax}) | R _{DS(on)} max | I _D |
|------------|---|----------------------------|--------------------|
| STD10NM65N | 710 V | < 0.48 Ω | 9 A |
| STF10NM65N | 710 V | < 0.48 Ω | 9 A ⁽¹⁾ |
| STP10NM65N | 710 V | < 0.48 Ω | 9 A |
| STU10NM65N | 710 V | < 0.48 Ω | 9 A |

1. Limited only by maximum temperature allowed

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Application

- Switching applications

Description

This series of devices implements the second generation of MDmesh™ Technology. This revolutionary Power MOSFET associates a new vertical structure to the Company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

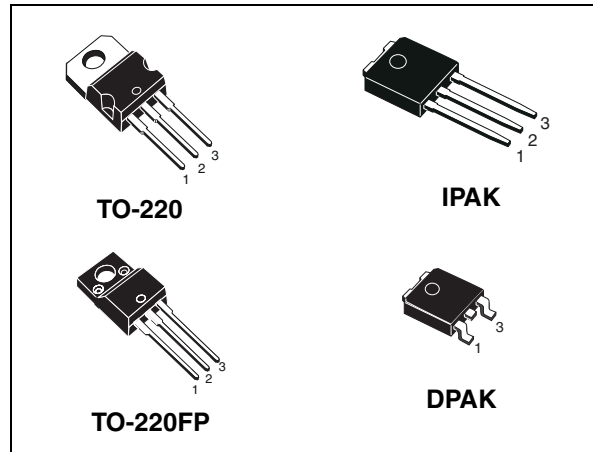


Figure 1. Internal schematic diagram

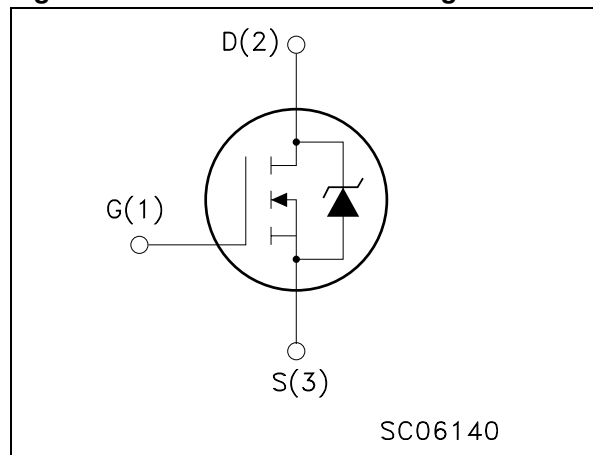


Table 1. Device summary

| Order codes | Marking | Package | Packaging |
|-------------|---------|----------|-------------|
| STD10NM65N | 10NM65N | DPAK | Tape & reel |
| STF10NM65N | 10NM65N | TO-220FP | Tube |
| STP10NM65N | 10NM65N | TO-220 | Tube |
| STU10NM65N | 10NM65N | IPAK | Tube |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | | Unit |
|--------------------------------|---|---------------------|--------------------|------|
| | | TO-220/IPAK DPAK | TO-220FP | |
| V _{DS} | Drain-source voltage (V _{GS} = 0) | 650 | | V |
| V _{GS} | Gate-source voltage | ± 25 | | V |
| I _D | Drain current (continuous) at T _C = 25 °C | 9 | g ⁽¹⁾ | A |
| I _D | Drain current (continuous) at T _C = 100 °C | 5.7 | 5.7 ⁽¹⁾ | A |
| I _{DM} ⁽²⁾ | Drain current (pulsed) | 36 | 36 ⁽¹⁾ | A |
| P _{TOT} | Total dissipation at T _C = 25 °C | 90 | 25 | W |
| dv/dt ⁽³⁾ | Peak diode recovery voltage slope | 15 | | V/ns |
| V _{ISO} | Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C = 25 °C) | -- | 2500 | V |
| T _{stg} | Storage temperature | -55 to 150 | | °C |
| T _j | Max. operating junction temperature | 150 | | °C |

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 9 A, di/dt ≤ 400 A/μs, V_{DD} = 80% V_{(BR)DSS}

Table 3. Thermal data

| Symbol | Parameter | TO-220 | IPAK | DPAK | TO-220FP | Unit |
|-----------------------|--|--------|------|------|----------|------|
| R _{thj-case} | Thermal resistance junction-case max | 1.38 | | | 5 | °C/W |
| R _{thj-pcb} | Thermal resistance junction-pcb max | -- | -- | 50 | -- | °C/W |
| R _{thj-amb} | Thermal resistance junction-amb max | 62.5 | 100 | -- | 62.5 | °C/W |
| T _l | Maximum lead temperature for soldering purpose | 300 | | | | °C |

Table 4. Avalanche characteristics

| Symbol | Parameter | Max value | Unit |
|-----------------|--|-----------|------|
| I _{AS} | Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max) | 3.5 | A |
| E _{AS} | Single pulse avalanche energy (starting T _j = 25 °C, I _D = I _{AS} , V _{DD} = 50 V) | 300 | mJ |

2 Electrical characteristics

($T_{CASE}=25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|-----------|--------------------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 1\text{ mA}$, $V_{GS} = 0$ | 650 | | | V |
| dv/dt (1) | Drain source voltage slope | $V_{DD} = 520\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 10\text{ V}$ | | 25 | | V/ns |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}$, @125 °C | | | 1 100 | μA μA |
| I_{GSS} | Gate-body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 2 | 3 | 4 | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 10\text{ V}$, $I_D = 4.5\text{ A}$ | | 0.43 | 0.48 | Ω |

1. Characteristics value at turn off on inductive load

Table 6. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------------------|-------------------------------|---|------|------|------|------|
| g_{fs} (1) | Forward transconductance | $V_{DS} = 15\text{ V}$, $I_D = 4.5\text{ A}$ | | 7.5 | | S |
| C_{iss} | Input capacitance | $V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$ | | 850 | | pF |
| C_{oss} | Output capacitance | | | 53 | | pF |
| C_{rss} | Reverse transfer capacitance | | | 4 | | pF |
| $C_{oss\text{ eq.}}$ (2) | Equivalent output capacitance | $V_{GS} = 0$, $V_{DS} = 0\text{ to }520\text{ V}$ | | 90 | | pF |
| Q_g | Total gate charge | $V_{DD} = 520\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 10\text{ V}$, (see Figure 19) | | 25 | | nC |
| Q_{gs} | Gate-source charge | | | 14 | | nC |
| Q_{gd} | Gate-drain charge | | | 4 | | nC |

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

| Symbol | Parameter | Test conditions | Min | Typ | Max | Unit |
|--------------|---------------------|---|-----|-----|-----|------|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 325\text{ V}$, $I_D = 4.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 18) | | 12 | | ns |
| t_r | Rise time | | | 8 | | ns |
| $t_{d(off)}$ | Turn-off delay time | | | | 50 | ns |
| t_f | Fall time | | | | 20 | ns |

Table 8. Source drain diode

| Symbol | Parameter | Test conditions | Min | Typ | Max | Unit |
|-----------------|-------------------------------|---|-----|-----|-----|---------------|
| I_{SD} | Source-drain current | | | | 9 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | | | 36 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 9\text{ A}$, $V_{GS} = 0$ | | | 1.3 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 20) | | 330 | | ns |
| Q_{rr} | Reverse recovery charge | | | | 3 | μC |
| I_{RRM} | Reverse recovery current | | | | 19 | A |
| t_{rr} | Reverse recovery time | $I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 20) | | 430 | | ns |
| Q_{rr} | Reverse recovery charge | | | | 4 | μC |
| I_{RRM} | Reverse recovery current | | | | 19 | A |

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

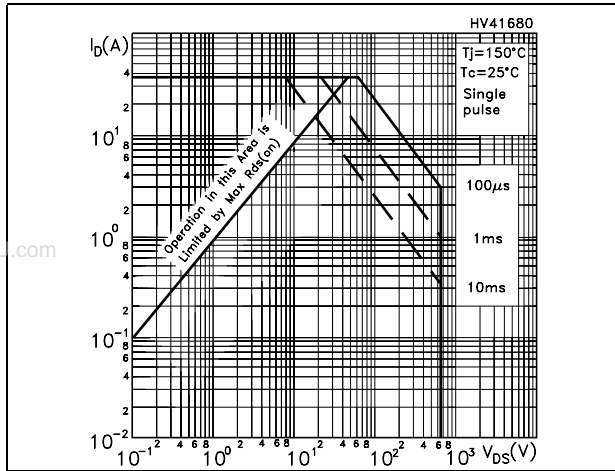


Figure 3. Thermal impedance for TO-220

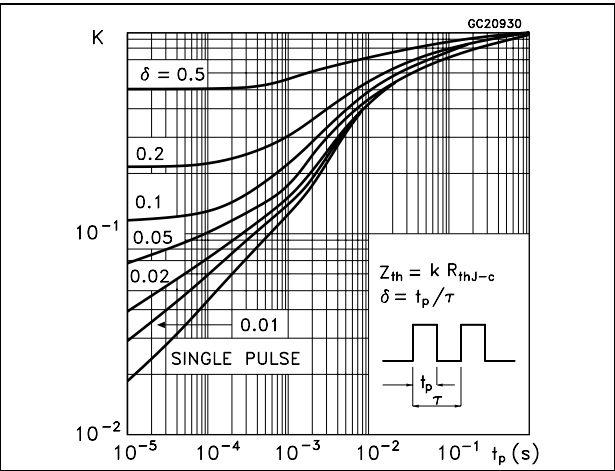


Figure 4. Safe operating area for TO-220FP

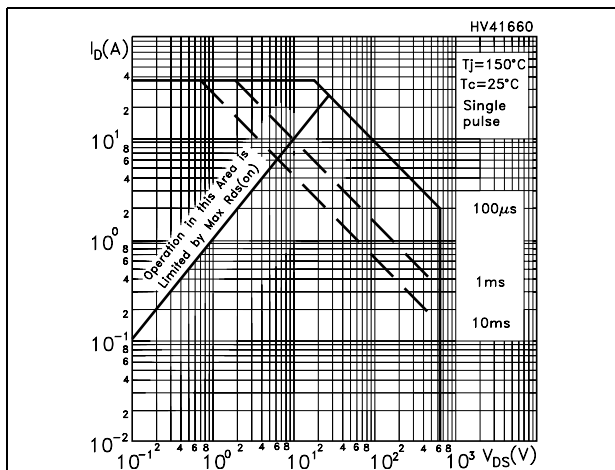


Figure 5. Thermal impedance for TO-220FP

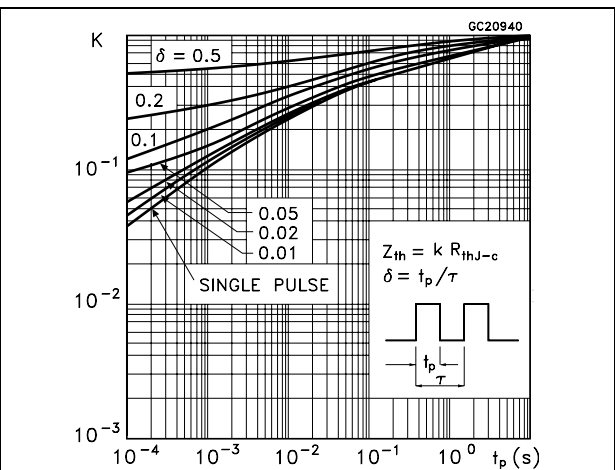


Figure 6. Safe operating area for DPAK/IPAK

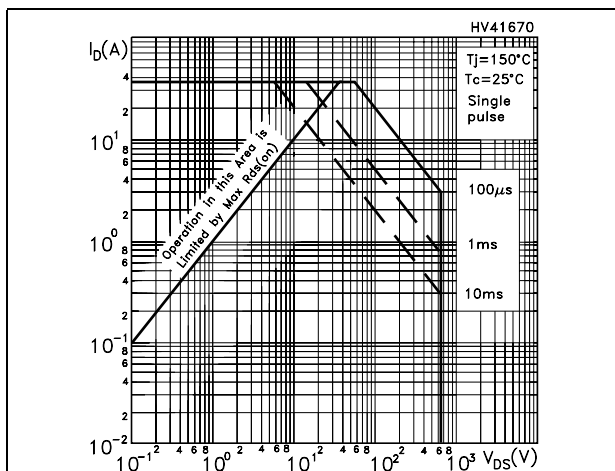


Figure 7. Thermal impedance for DPAK/IPAK

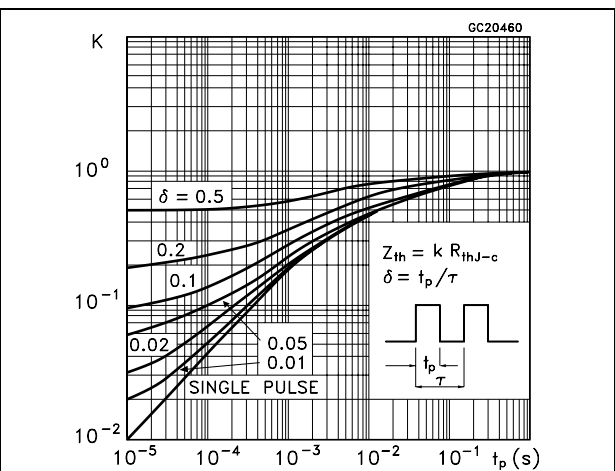


Figure 8. Output characteristics

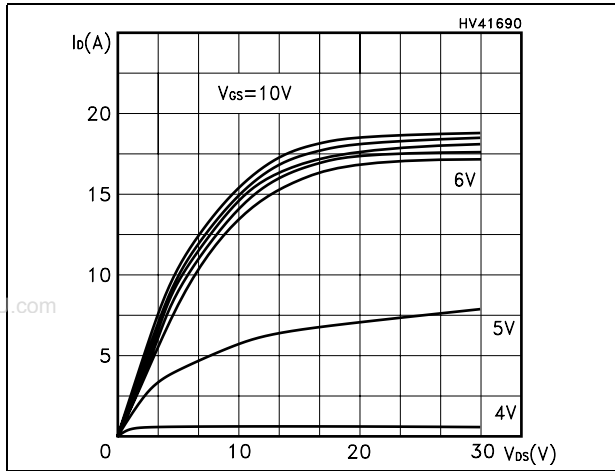


Figure 9. Transfer characteristics

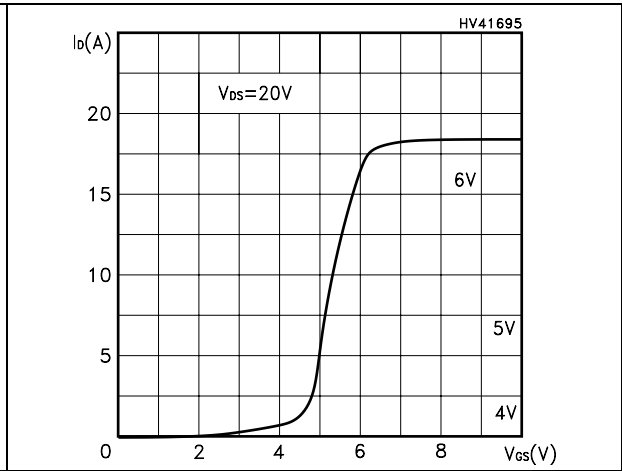


Figure 10. Transconductance

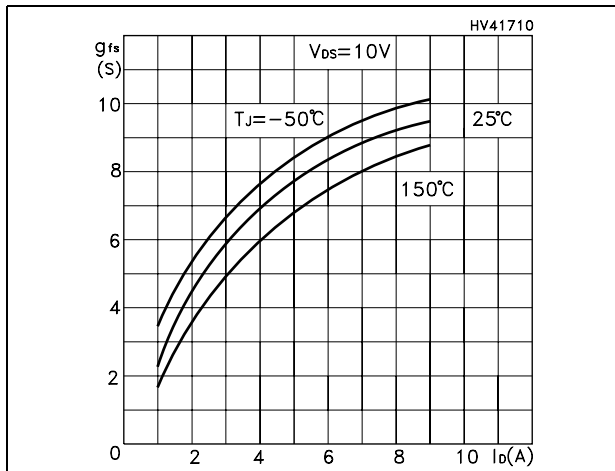


Figure 11. Static drain-source on resistance

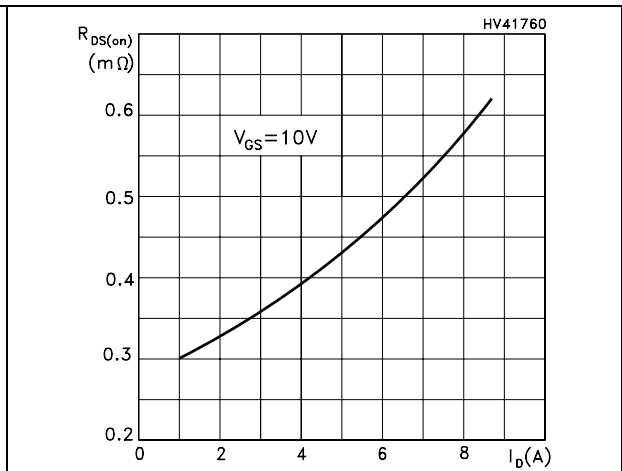


Figure 12. Gate charge vs gate source voltage

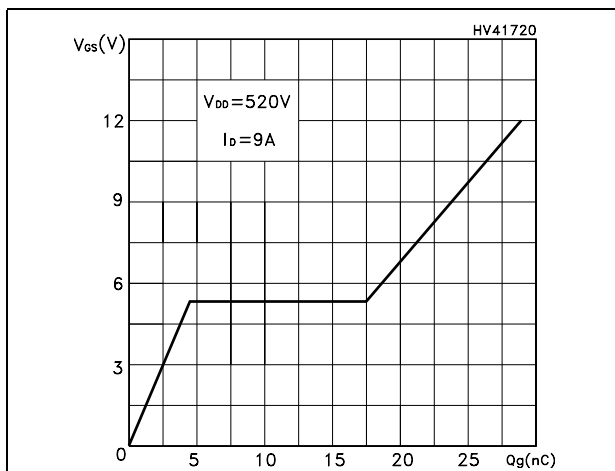


Figure 13. Capacitance variations

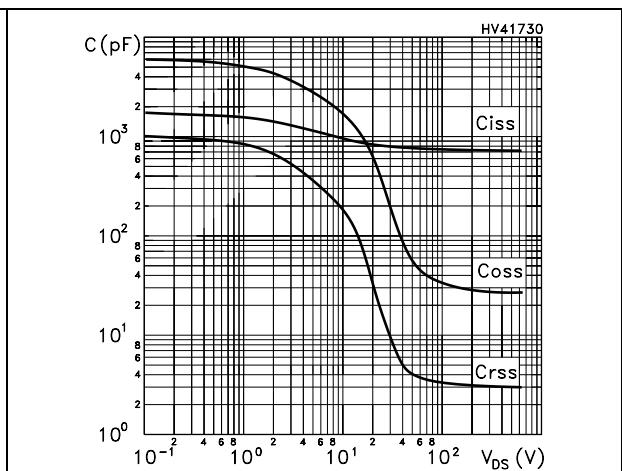


Figure 14. Normalized gate threshold voltage vs temperature

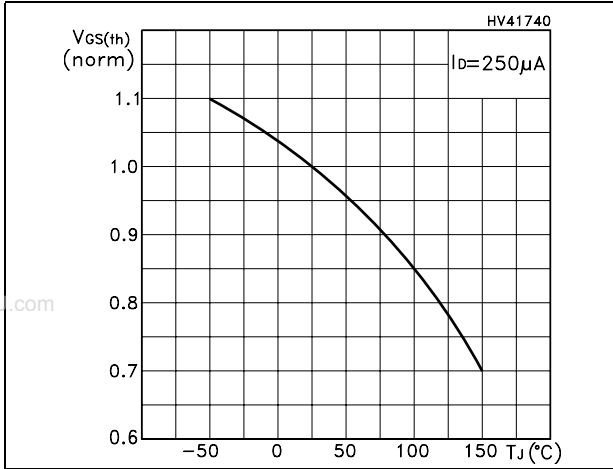


Figure 15. Normalized on resistance vs temperature

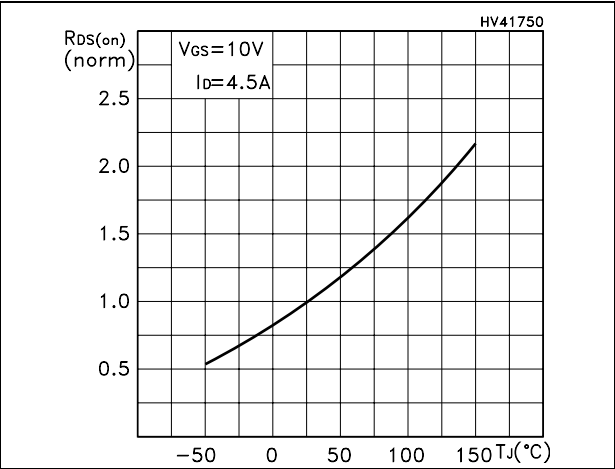


Figure 16. Source-drain diode forward characteristics

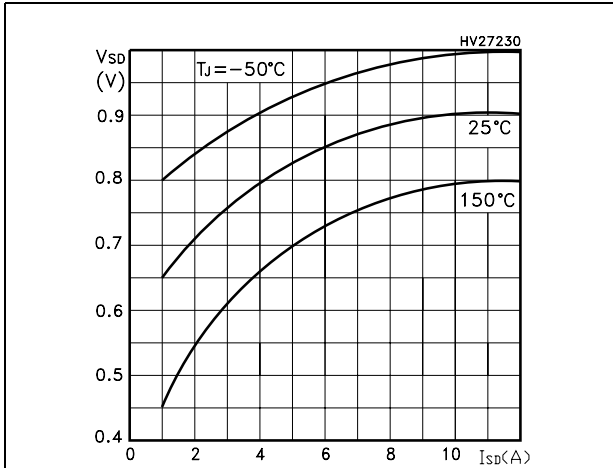
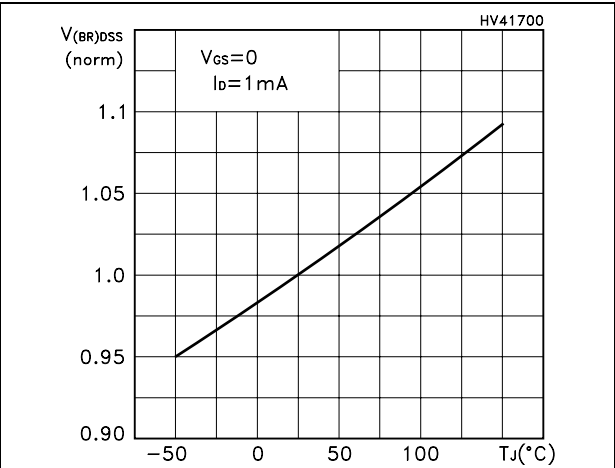


Figure 17. Normalized BV_{DSS} vs temperature



3 Test circuit

Figure 18. Switching times test circuit for resistive load

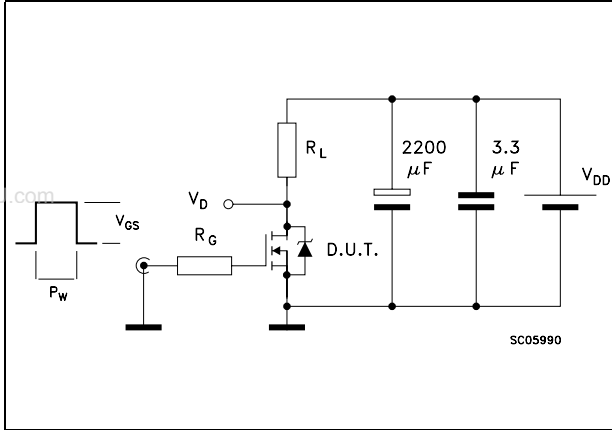


Figure 19. Gate charge test circuit

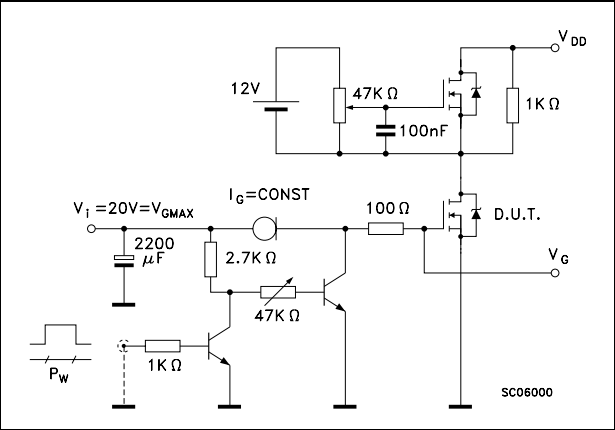


Figure 20. Test circuit for inductive load switching and diode recovery times

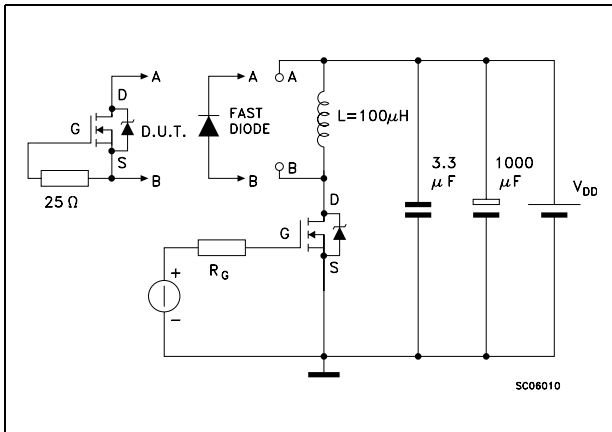


Figure 21. Unclamped inductive load test circuit

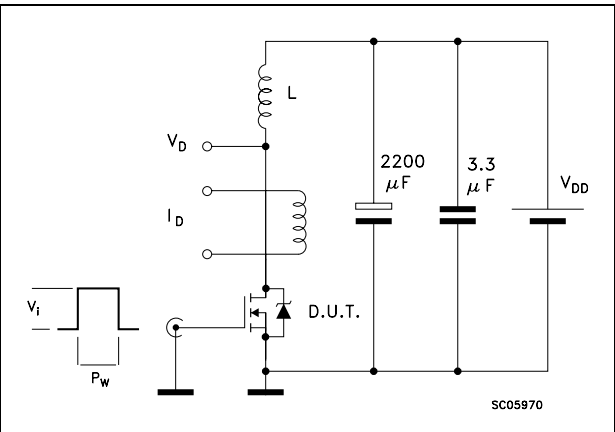


Figure 22. Unclamped inductive waveform

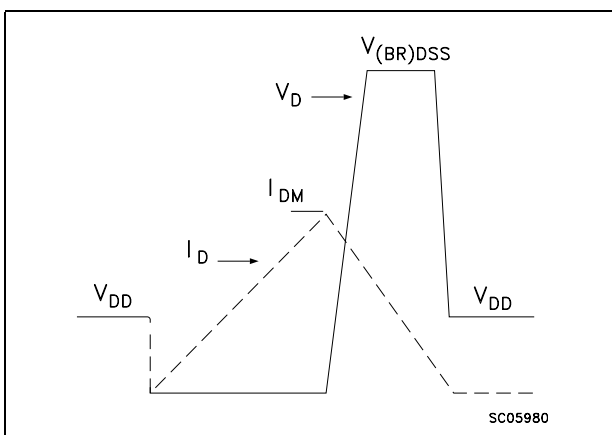
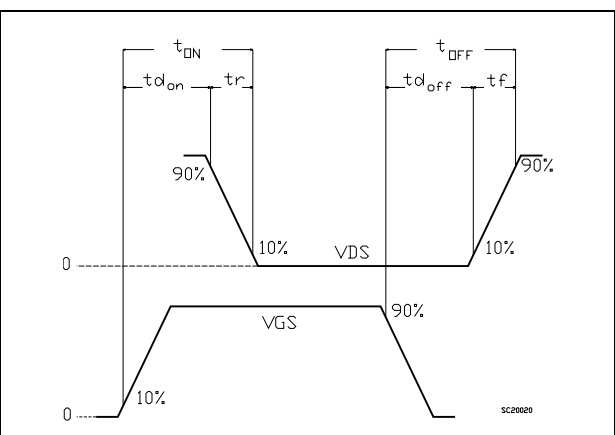


Figure 23. Switching time waveform



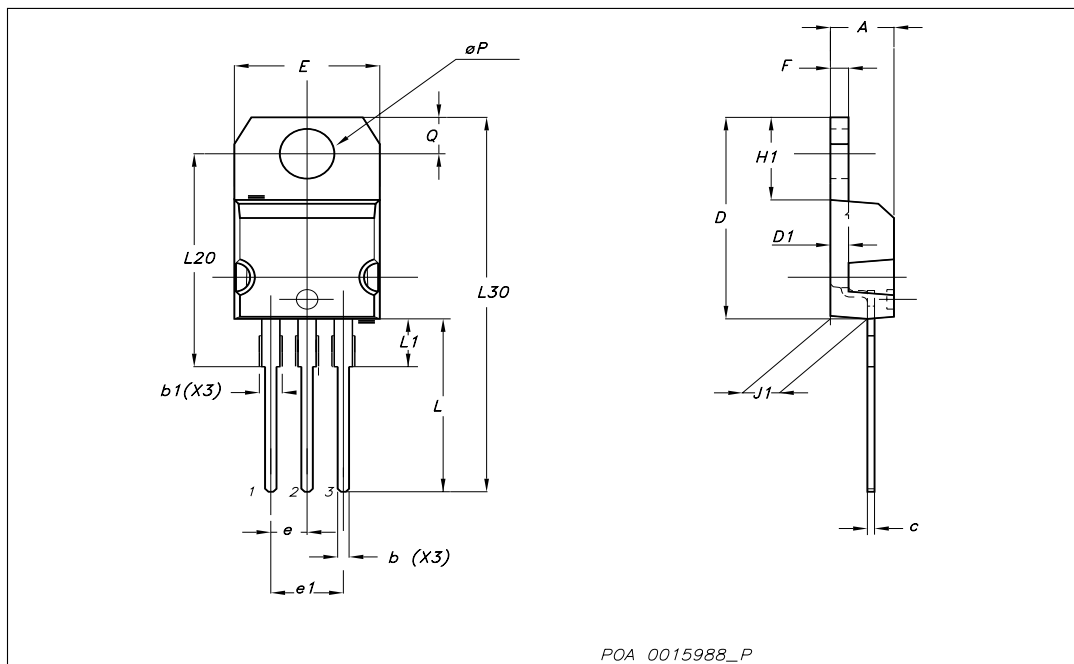
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 mechanical data

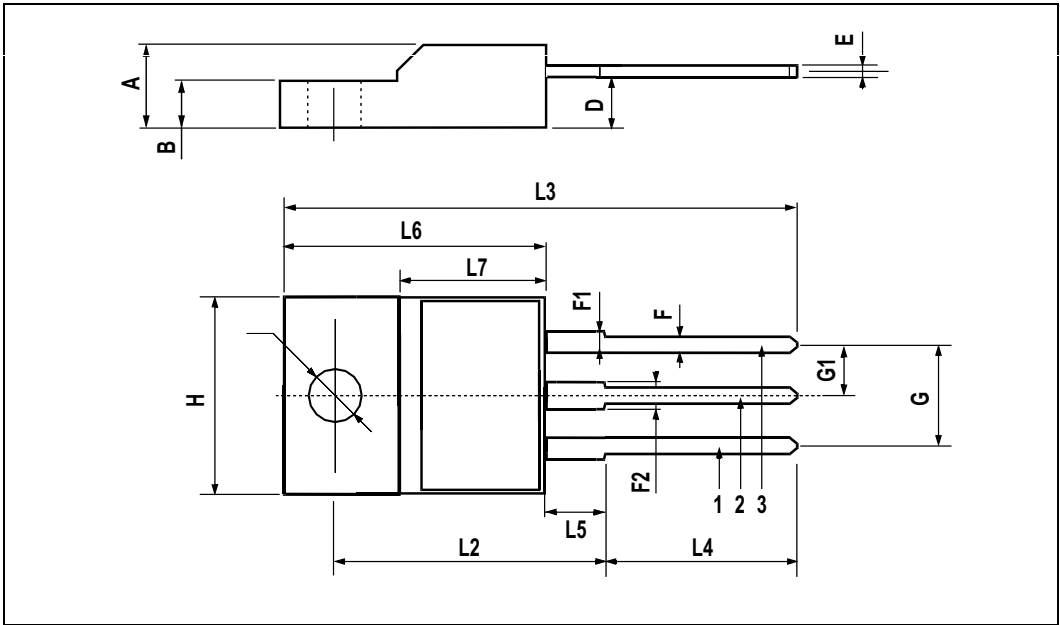
| Dim | mm | | | inch | | |
|-----|-------|-------|-------|-------|-------|-------|
| | Min | Typ | Max | Min | Typ | Max |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| c | 0.49 | | 0.70 | 0.019 | | 0.027 |
| D | 15.25 | | 15.75 | 0.6 | | 0.62 |
| D1 | | 1.27 | | | 0.050 | |
| E | 10 | | 10.40 | 0.393 | | 0.409 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| F | 1.23 | | 1.32 | 0.048 | | 0.051 |
| H1 | 6.20 | | 6.60 | 0.244 | | 0.256 |
| J1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L20 | | 16.40 | | | 0.645 | |
| L30 | | 28.90 | | | 1.137 | |
| ∅P | 3.75 | | 3.85 | 0.147 | | 0.151 |
| Q | 2.65 | | 2.95 | 0.104 | | 0.116 |

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TO-220FP MECHANICAL DATA

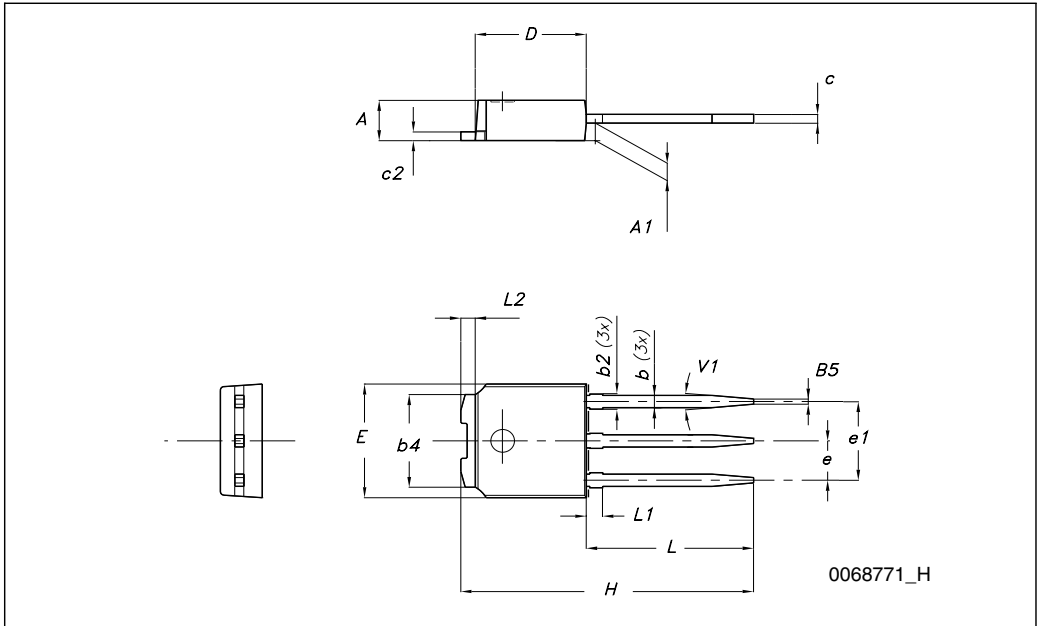
| DIM. | mm. | | | inch | | |
|------|------|-----|------|-------|-------|-------|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| B | 2.5 | | 2.7 | 0.098 | | 0.106 |
| D | 2.5 | | 2.75 | 0.098 | | 0.108 |
| E | 0.45 | | 0.7 | 0.017 | | 0.027 |
| F | 0.75 | | 1 | 0.030 | | 0.039 |
| F1 | 1.15 | | 1.7 | 0.045 | | 0.067 |
| F2 | 1.15 | | 1.7 | 0.045 | | 0.067 |
| G | 4.95 | | 5.2 | 0.195 | | 0.204 |
| G1 | 2.4 | | 2.7 | 0.094 | | 0.106 |
| H | 10 | | 10.4 | 0.393 | | 0.409 |
| L2 | | 16 | | | 0.630 | |
| L3 | 28.6 | | 30.6 | 1.126 | | 1.204 |
| L4 | 9.8 | | 10.6 | .0385 | | 0.417 |
| L5 | 2.9 | | 3.6 | 0.114 | | 0.141 |
| L6 | 15.9 | | 16.4 | 0.626 | | 0.645 |
| L7 | 9 | | 9.3 | 0.354 | | 0.366 |
| Ø | 3 | | 3.2 | 0.118 | | 0.126 |



TO-251 (IPAK) mechanical data

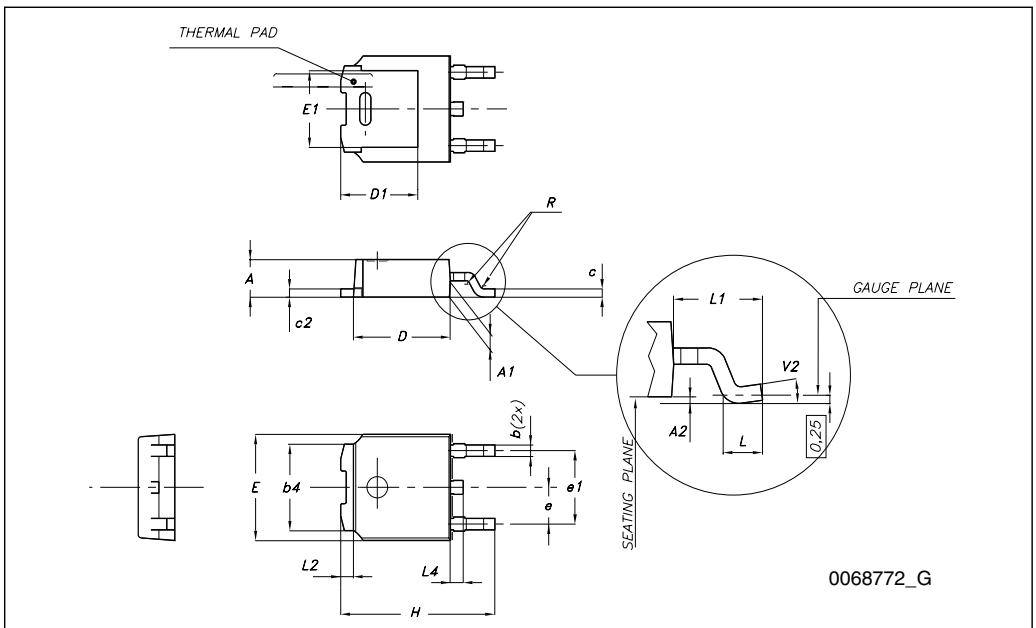
| DIM. | mm. | | |
|------|------|-------|------|
| | min. | typ | max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| b | 0.64 | | 0.90 |
| b2 | | | 0.95 |
| b4 | 5.20 | | 5.40 |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| E | 6.40 | | 6.60 |
| e | | 2.28 | |
| e1 | 4.40 | | 4.60 |
| H | | 16.10 | |
| L | 9.00 | | 9.40 |
| (L1) | 0.80 | | 1.20 |
| L2 | | 0.80 | |
| V1 | | 10° | |

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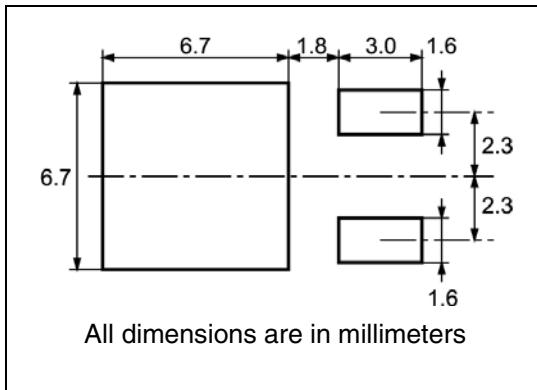
TO-252 (DPAK) mechanical data

| DIM. | mm. | | |
|------|------|------|-------|
| | min. | typ | max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| A2 | 0.03 | | 0.23 |
| b | 0.64 | | 0.90 |
| b4 | 5.20 | | 5.40 |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| D1 | | 5.10 | |
| E | 6.40 | | 6.60 |
| E1 | | 4.70 | |
| e | | 2.28 | |
| e1 | 4.40 | | 4.60 |
| H | 9.35 | | 10.10 |
| L | 1 | | |
| L1 | | 2.80 | |
| L2 | | 0.80 | |
| L4 | 0.60 | | 1 |
| R | | 0.20 | |
| V2 | 0° | | 8° |



5 Package mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

| DIM. | mm | | inch | |
|------|------|------|-------|--------|
| | MIN. | MAX. | MIN. | MAX. |
| A | | 330 | | 12.992 |
| B | 1.5 | | 0.059 | |
| C | 12.8 | 13.2 | 0.504 | 0.520 |
| D | 20.2 | | 0.795 | |
| G | 16.4 | 18.4 | 0.645 | 0.724 |
| N | 50 | | 1.968 | |
| T | | 22.4 | | 0.881 |

| BASE QTY | BULK QTY |
|----------|----------|
| 2500 | 2500 |

| DIM. | mm | | inch | |
|------|------|------|-------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A0 | 6.8 | 7 | 0.267 | 0.275 |
| B0 | 10.4 | 10.6 | 0.409 | 0.417 |
| B1 | | 12.1 | | 0.476 |
| D | 1.5 | 1.6 | 0.059 | 0.063 |
| D1 | 1.5 | | 0.059 | |
| E | 1.65 | 1.85 | 0.065 | 0.073 |
| F | 7.4 | 7.6 | 0.291 | 0.299 |
| K0 | 2.55 | 2.75 | 0.100 | 0.108 |
| P0 | 3.9 | 4.1 | 0.153 | 0.161 |
| P1 | 7.9 | 8.1 | 0.311 | 0.319 |
| P2 | 1.9 | 2.1 | 0.075 | 0.082 |
| R | 40 | | 1.574 | |
| W | 15.7 | 16.3 | 0.618 | 0.641 |

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

For machine ref. only including draft and radii concentric around B0

TRL

FEED DIRECTION

Bending radius

R min.

6 Revision history

Table 9. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 26-Oct-2007 | 1 | Initial release. |
| 07-Feb-2008 | 2 | Document status promoted from preliminary data to datasheet. |

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